

N-Channel 100-V (D-S) MOSFET

Key Features:

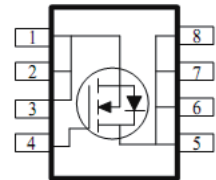
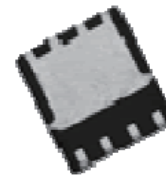
- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits



DFN3x3-8L



PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
100	26 @ $V_{GS} = 10V$	9.5
	36 @ $V_{GS} = 4.5V$	8.1

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_A = 25^\circ C$	I_D	9.5	A
	$T_A = 70^\circ C$		7.2	
Pulsed Drain Current ^b		I_{DM}	40	
Continuous Source Current (Diode Conduction) ^a		I_S	4.8	A
Power Dissipation ^a	$T_A = 25^\circ C$	P_D	3.5	W
	$T_A = 70^\circ C$		2	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	$R_{\theta JA}$	35	$^\circ C/W$
	Steady State		81	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

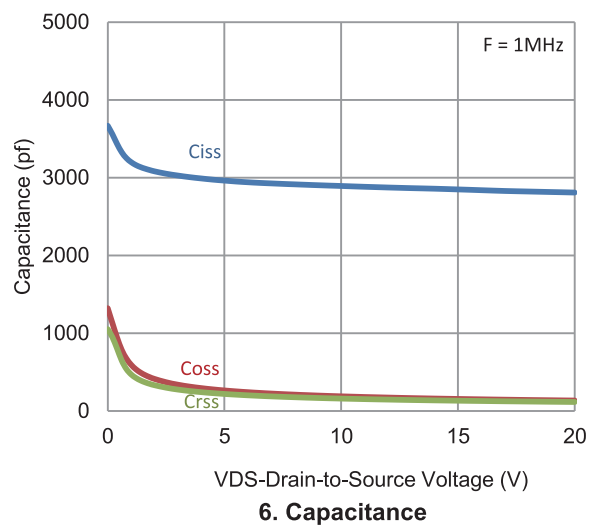
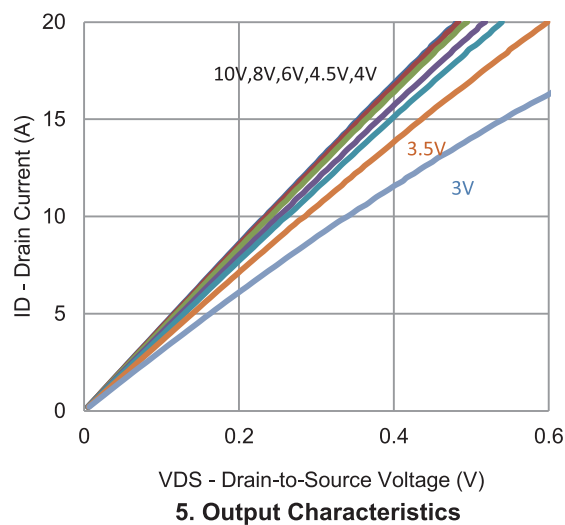
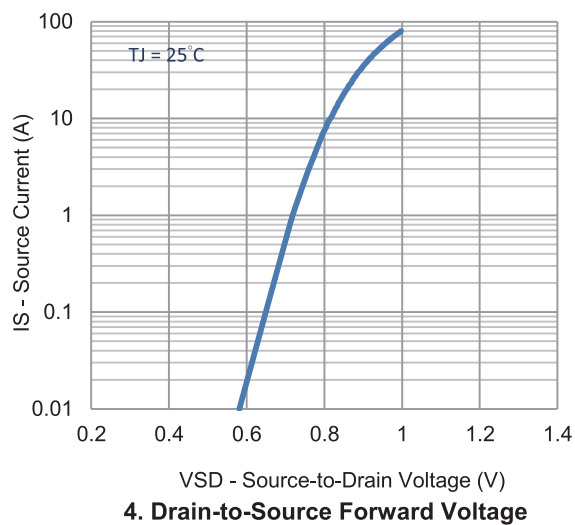
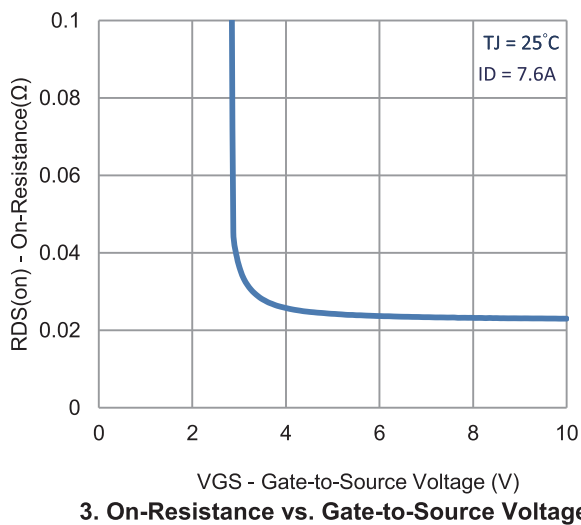
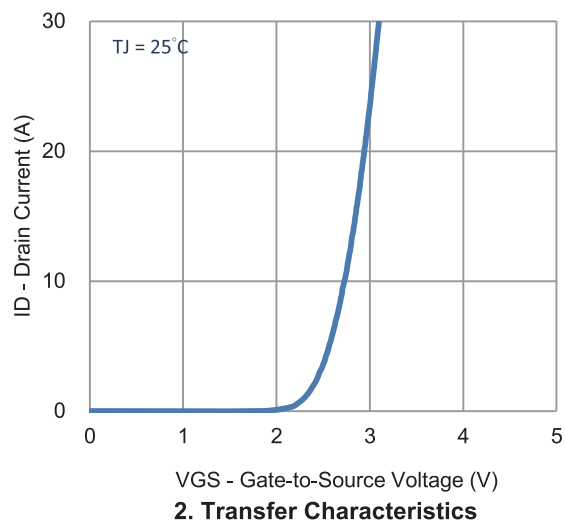
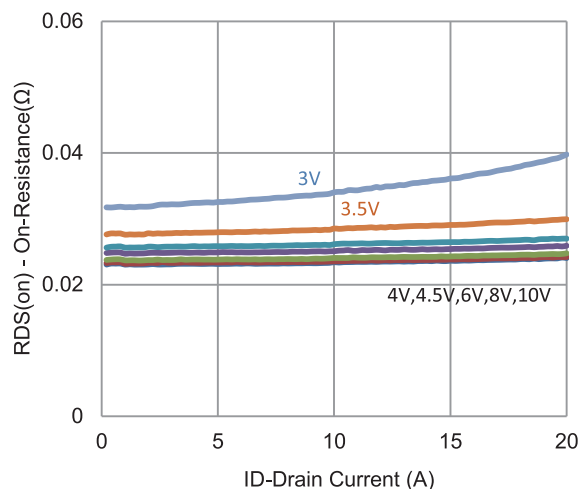
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	15			A
Drain-Source On-Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 7.6 A$			26	m Ω
		$V_{GS} = 4.5 V, I_D = 6.3 A$			36	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 V, I_D = 7.8 A$		31		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.4 A, V_{GS} = 0 V$		0.76		V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 50 V, V_{GS} = 4.5 V,$ $I_D = 7.6 A$		30		nC
Gate-Source Charge	Q_{gs}			11		
Gate-Drain Charge	Q_{gd}			10		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 50 V, R_L = 6.6 \Omega, I_D = 7.6 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		10		ns
Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(off)}$			90		
Fall Time	t_f			25		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 Mhz$		2848		pF
Output Capacitance	C_{oss}			154		
Reverse Transfer Capacitance	C_{rss}			131		

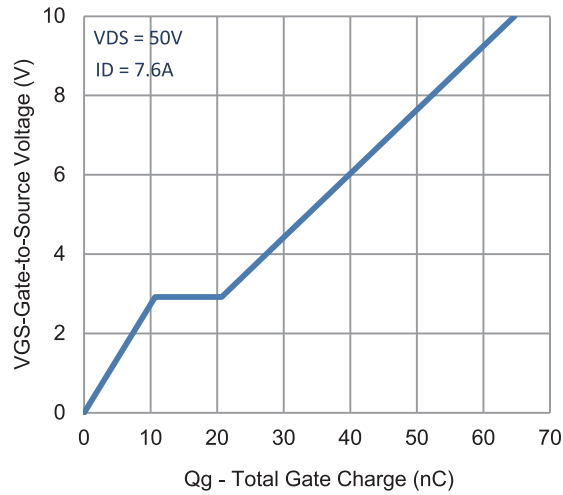
Notes

- a. Pulse test: PW $\leq$ 300 μ s duty cycle $\leq$ 2%.
- b. Guaranteed by design, not subject to production testing.

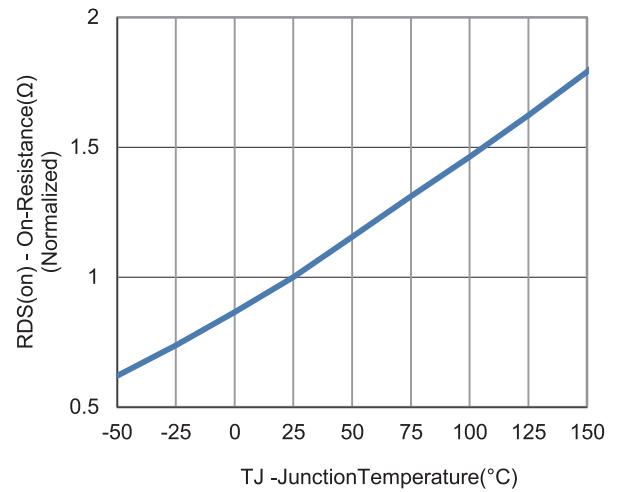
Typical Electrical Characteristics



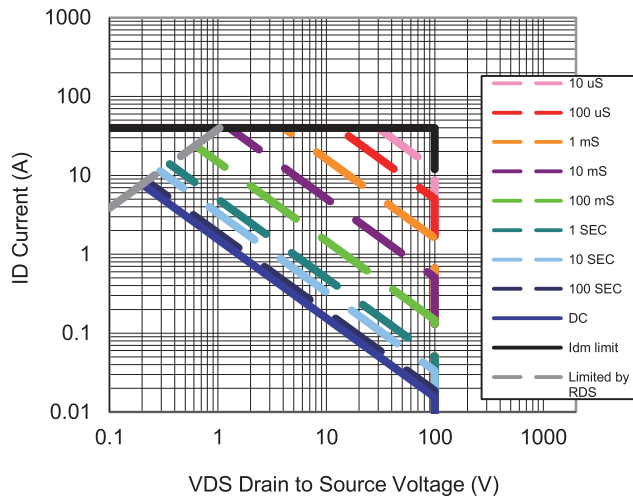
Typical Electrical Characteristics



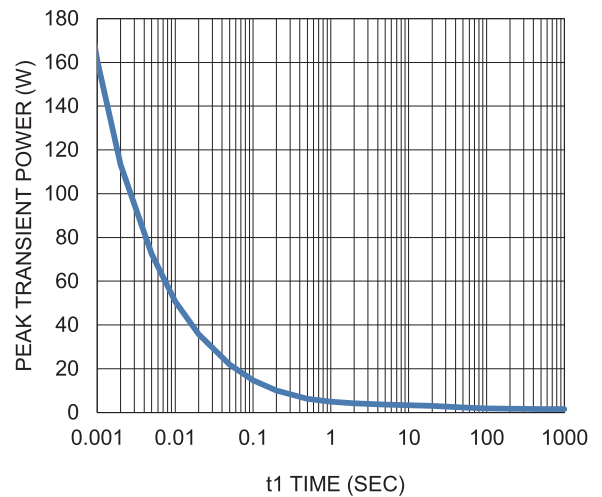
7. Gate Charge



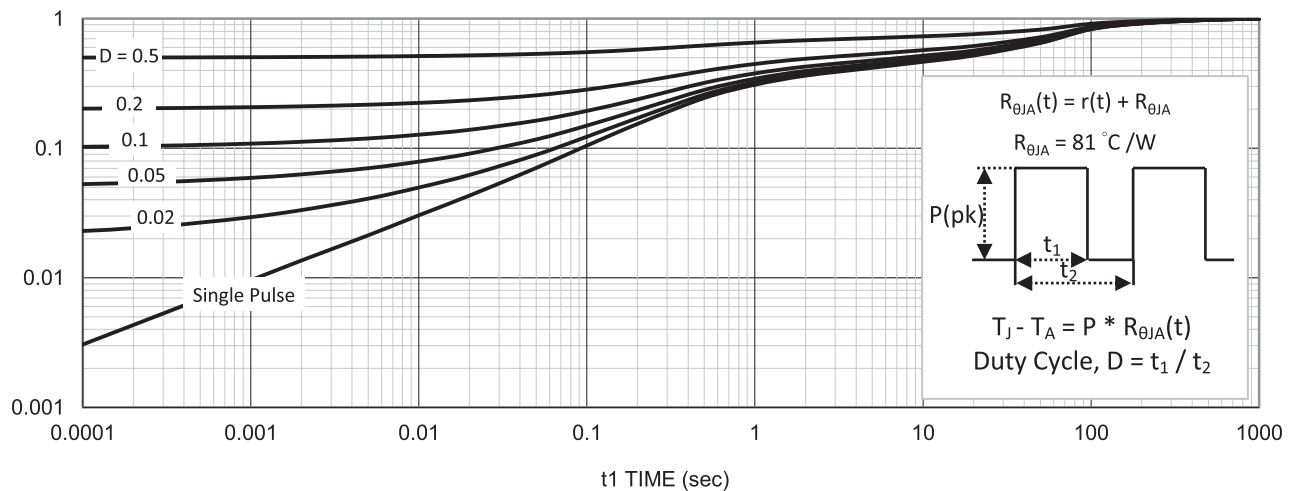
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area

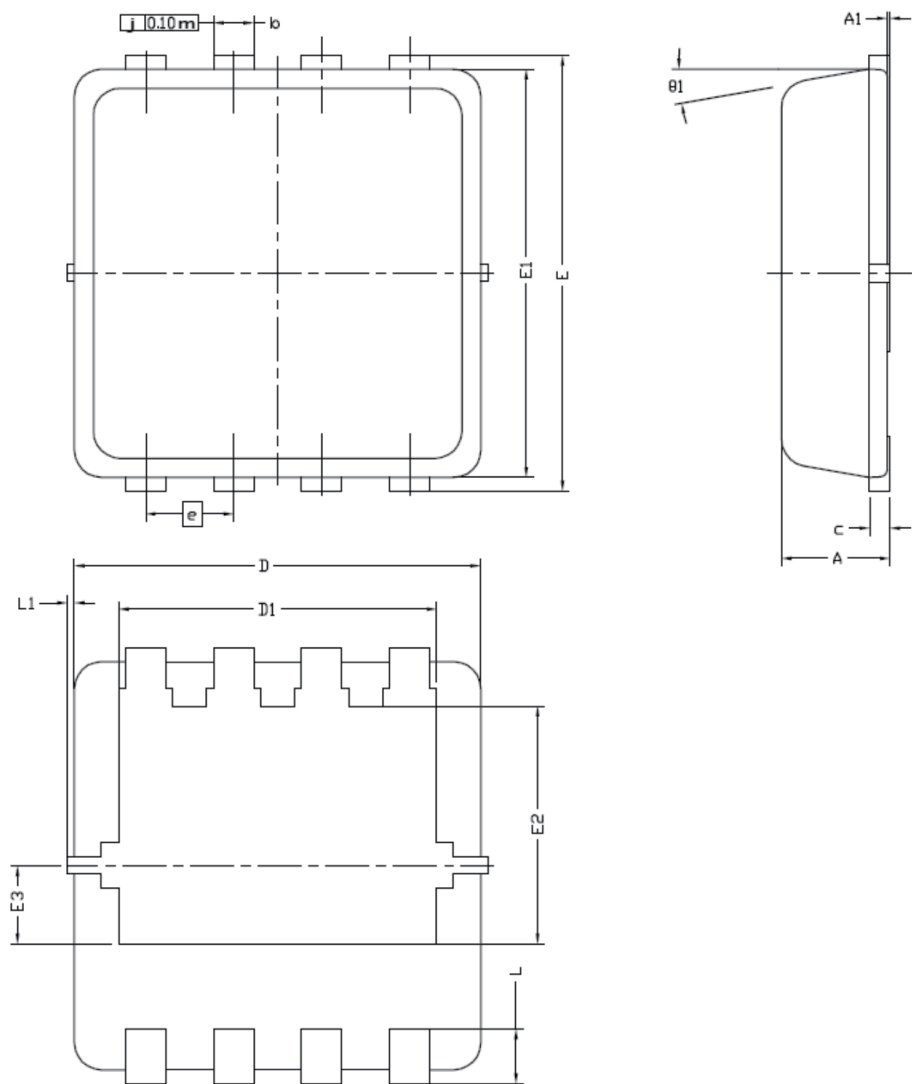


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



DIM,	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0,700	0,80	0,900	0,0276	0,0315	0,0354
A1	0,00	---	0,05	0,000	---	0,002
b	0,24	0,30	0,35	0,009	0,012	0,014
c	0,10	0,152	0,25	0,004	0,006	0,010
D	3,00 BSC			0,118 BSC		
D1	2,35 BSC			0,093 BSC		
E	3,20 BSC			0,126 BSC		
E1	3,00 BSC			0,118 BSC		
E2	1,75 BSC			0,069 BSC		
E3	0,575 BSC			0,023 BSC		
e	0,65 BSC			0,026 BSC		
L	0,30	0,40	0,50	0,0118	0,0157	0,0197
L1	0	---	0,100	0	---	0,004
θ1	0°	10°	12°	0°	10°	12°